

FCPF190N65S3R0L

Power MOSFET, N-Channel, SUPERFET® III, Easy Drive, 650 V, 17 A, 190 mΩ

Description

SUPERFET III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate. Consequently, SUPERFET III MOSFET Easy drive series helps manage EMI issues and allows for easier design implementation.

Features

- 700 V @ $T_J = 150^\circ\text{C}$
- Typ. $R_{DS(on)} = 159 \text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_g = 33 \text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(\text{eff.})} = 300 \text{ pF}$)
- 100% Avalanche Tested
- This Device is Pb-Free and is RoHS Compliant

Applications

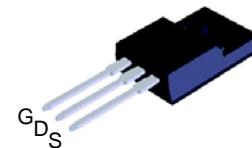
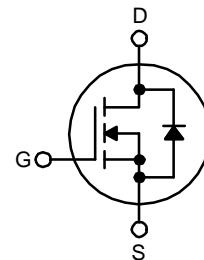
- Computing / Display Power Supplies
- Telecom / Server Power Supplies
- Industrial Power Supplies
- Lighting / Charger / Adapter



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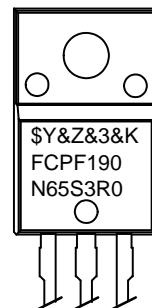
www.onsemi.com

V_{DSS}	$R_{DS(on)\text{ MAX}}$	$I_D \text{ MAX}$
650 V	190 mΩ @ 10 V	17 A



TO-220
CASE 340BF

MARKING DIAGRAM



\$Y = ON Semiconductor Logo
&Z = Assembly Plant Code
&3 = Numeric Date Code
&K = Lot Code
FCPF190N65S3R0 = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FCPF190N65S3R0L

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		FCPF190N65S3R0L	Unit
V_{DSS}	Drain to Source Voltage		650	V
V_{GSS}	Gate to Source Voltage	DC	± 30	V
		AC ($f > 1 \text{ Hz}$)	± 30	V
I_D	Drain Current	Continuous ($T_C = 25^\circ\text{C}$)	17*	A
		Continuous ($T_C = 100^\circ\text{C}$)	11*	
I_{DM}	Drain Current	Pulsed (Note 1)	42.5*	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		76	mJ
I_{AS}	Avalanche Current (Note 2)		2.5	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		1.44	mJ
dv/dt	MOSFET dv/dt		100	V/ns
	Peak Diode Recovery dv/dt (Note 3)		20	
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	33	W
		Derate Above 25°C	1.15	$\text{W}/^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

*Drain current limited by maximum junction temperature.

1. Repetitive rating: pulse-width limited by maximum junction temperature.

2. $I_{AS} = 2.5 \text{ A}$, $R_G = 25 \Omega$, starting $T_J = 25^\circ\text{C}$.

3. $I_{SD} \leq 8.5 \text{ A}$, $di/dt \leq 200 \text{ A/ms}$, $V_{DD} \leq 400 \text{ V}$, starting $T_J = 25^\circ\text{C}$.

THERMAL CHARACTERISTICS

Symbol	Parameter	FCPF190N65S3R0L	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	3.76	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCPF190N65S3R0L	FCPF190N65S3R0	TO-220F	Tube	N/A	N/A	50 Units

FCPF190N65S3R0L

ELECTRICAL CHARACTERISTICS OF THE IGBT ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV_{DSS}	Drain to Source Breakdown Voltage	$V_{\text{GS}} = 0 \text{ V}$, $I_D = 1 \text{ mA}$, $T_J = 25^\circ\text{C}$	650	–	–	V
		$V_{\text{GS}} = 0 \text{ V}$, $I_D = 1 \text{ mA}$, $T_J = 150^\circ\text{C}$	700	–	–	V
$\Delta \text{BV}_{\text{DSS}} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 1 \text{ mA}$, Referenced to 25°C	–	0.6	–	$^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}} = 650 \text{ V}$, $V_{\text{GS}} = 0 \text{ V}$	–	–	1	μA
		$V_{\text{DS}} = 520 \text{ V}$, $T_C = 125^\circ\text{C}$	–	0.89	–	
I_{GSS}	Gate to Body Leakage Current	$V_{\text{GS}} = \pm 30 \text{ V}$, $V_{\text{DS}} = 0 \text{ V}$	–	–	± 100	nA

ON CHARACTERISTICS

$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{GS}} = V_{\text{DS}}$, $I_D = 1.7 \text{ mA}$	2.5	–	4.5	V
$R_{\text{DS(on)}}$	Static Drain to Source On Resistance	$V_{\text{GS}} = 10 \text{ V}$, $I_D = 8.5 \text{ A}$	–	159	190	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{\text{DS}} = 20 \text{ V}$, $I_D = 8.5 \text{ A}$	–	10	–	S

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{\text{DS}} = 400 \text{ V}$, $V_{\text{GS}} = 0 \text{ V}$, $f = 1 \text{ MHz}$	–	1350	–	pF
C_{oss}	Output Capacitance		–	30	–	pF
$C_{\text{oss(ef)}}(e)$	Effective Output Capacitance	$V_{\text{DS}} = 0 \text{ V}$ to 400 V , $V_{\text{GS}} = 0 \text{ V}$	–	300	–	pF
$C_{\text{oss(er)}}$	Energy Related Output Capacitance	$V_{\text{DS}} = 0 \text{ V}$ to 400 V , $V_{\text{GS}} = 0 \text{ V}$	–	43	–	pF
$Q_{\text{g(tot)}}$	Total Gate Charge at 10V	$V_{\text{DS}} = 400 \text{ V}$, $I_D = 8.5 \text{ A}$, $V_{\text{GS}} = 10 \text{ V}$ (Note 4)	–	33	–	nC
Q_{gs}	Gate to Source Gate Charge		–	7.9	–	nC
Q_{gd}	Gate to Drain "Miller" Charge		–	14	–	nC
ESR	Equivalent Series Resistance	$f = 1 \text{ MHz}$	–	0.5	–	Ω

SWITCHING CHARACTERISTICS

$t_{\text{d(on)}}$	Turn-On Delay Time	$V_{\text{DD}} = 400 \text{ V}$, $I_D = 8.5 \text{ A}$, $V_{\text{GS}} = 10 \text{ V}$, $R_g = 4.7 \Omega$ (Note 4)	–	17	–	ns
t_r	Turn-On Rise Time		–	16	–	ns
$t_{\text{d(off)}}$	Turn-Off Delay Time		–	42	–	ns
t_f	Turn-Off Fall Time		–	6	–	ns

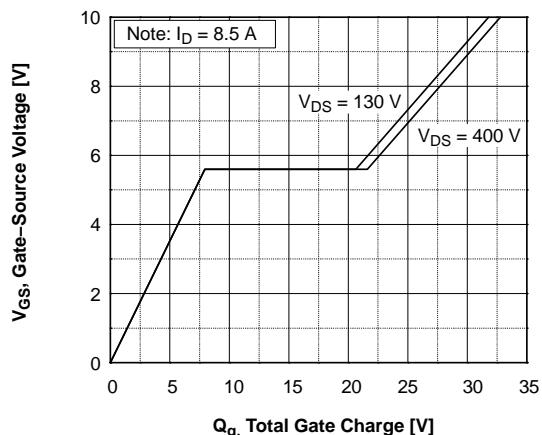
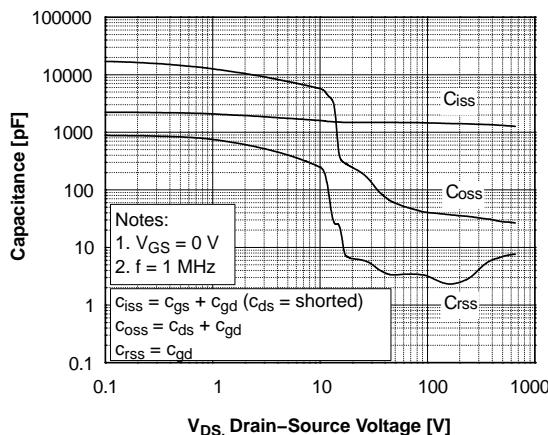
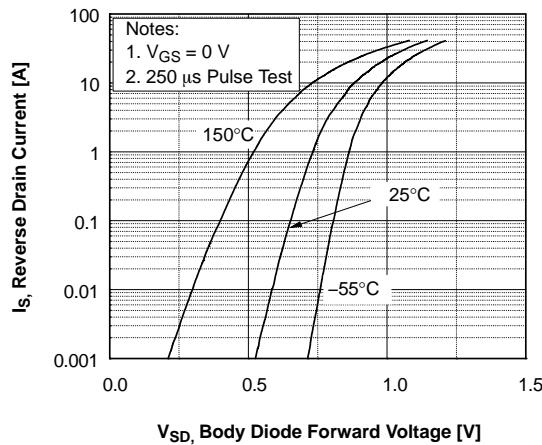
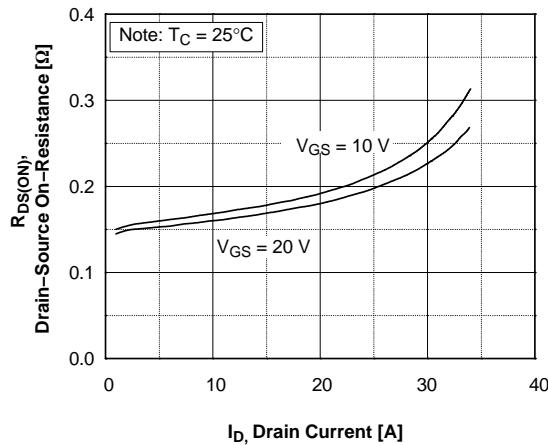
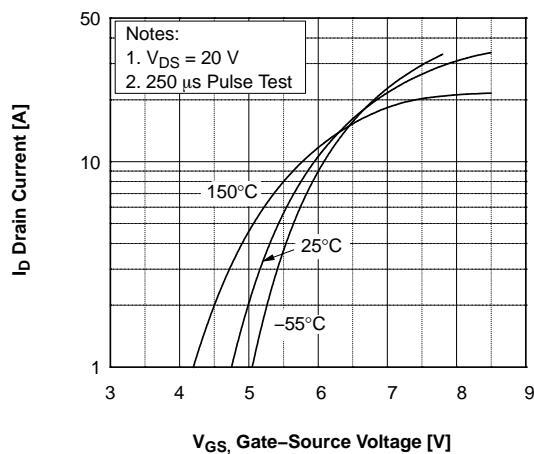
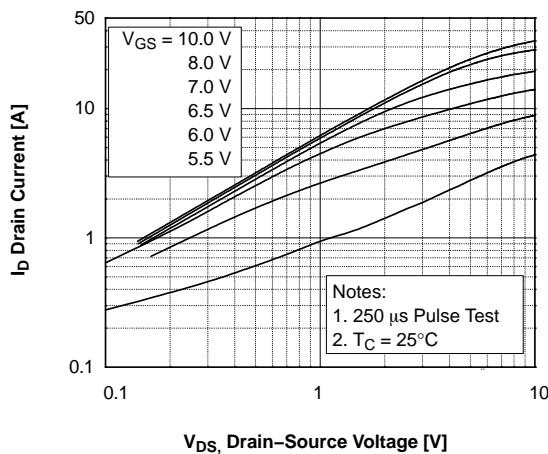
SOURCE-DRAIN DIODE CHARACTERISTICS

I_S	Maximum Continuous Source to Drain Diode Forward Current	–	–	17	A	
I_{SM}	Maximum Pulsed Source to Drain Diode Forward Current	–	–	42.5	A	
V_{SD}	Source to Drain Diode Forward Voltage	$V_{\text{GS}} = 0 \text{ V}$, $I_{\text{SD}} = 8.5 \text{ A}$	–	–	1.2	V
t_{rr}	Reverse Recovery Time	$V_{\text{GS}} = 0 \text{ V}$, $I_{\text{SD}} = 8.5 \text{ A}$, $dI_F/dt = 100 \text{ A/ms}$	–	313	–	ns
Q_{rr}	Reverse Recovery Charge		–	4.9	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS



TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

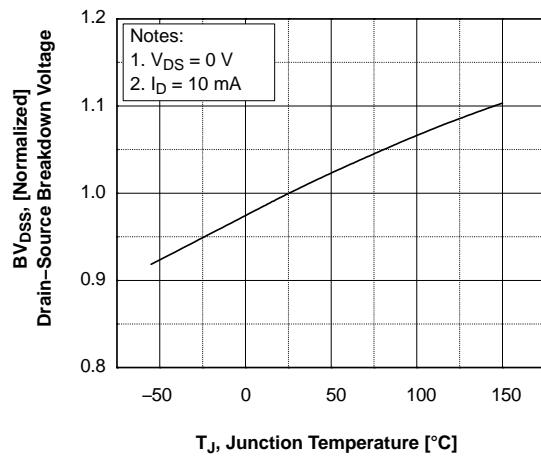


Figure 7. Breakdown Voltage Variation vs. Temperature

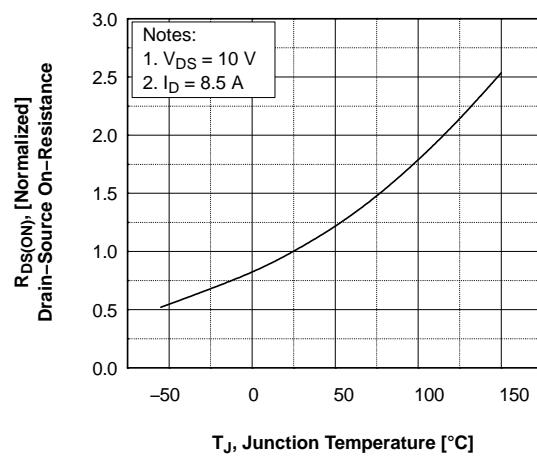


Figure 8. On-Resistance Variation vs. Temperature

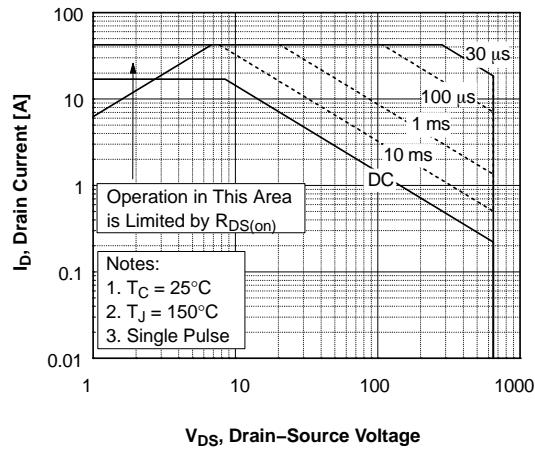


Figure 9. Maximum Safe Operating Area

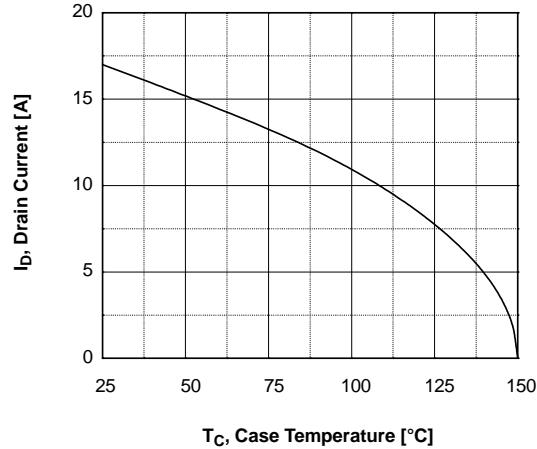


Figure 10. Maximum Drain Current vs. Case Temperature

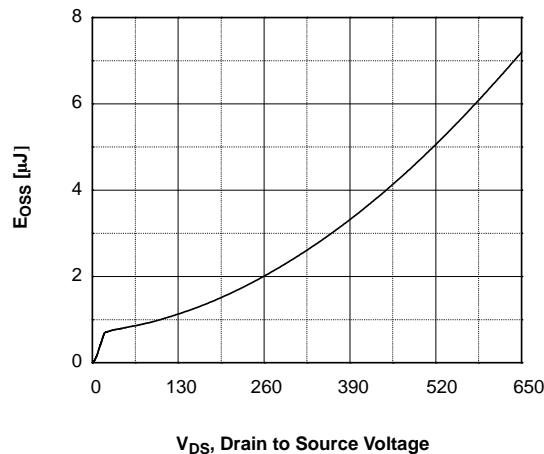


Figure 11. E_{oss} vs. Drain to Source Voltage

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

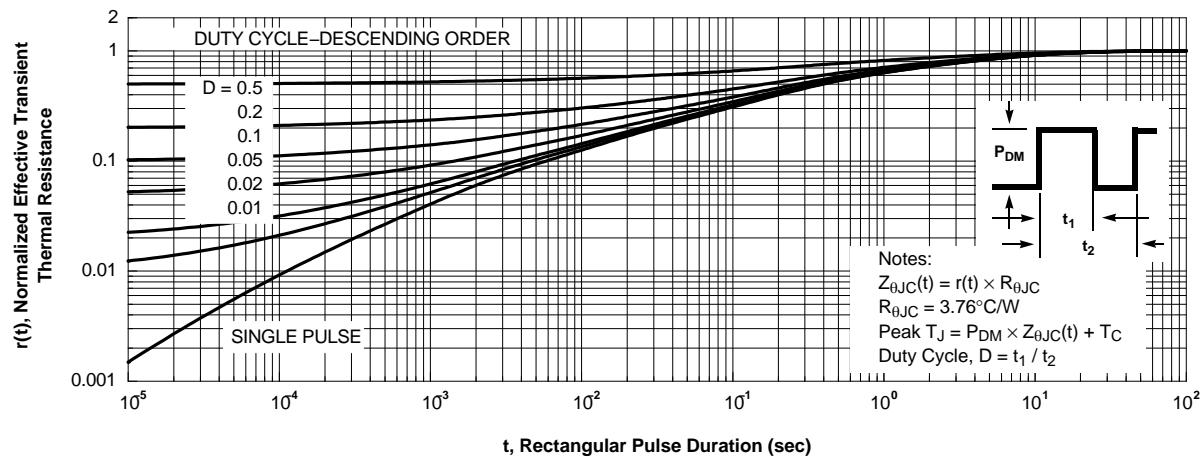


Figure 12. Transient Thermal Response Curve

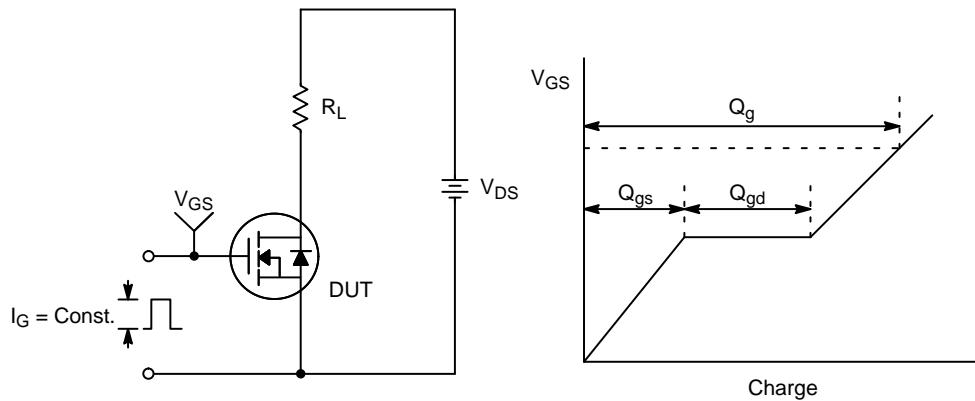


Figure 13. Gate Charge Test Circuit & Waveform

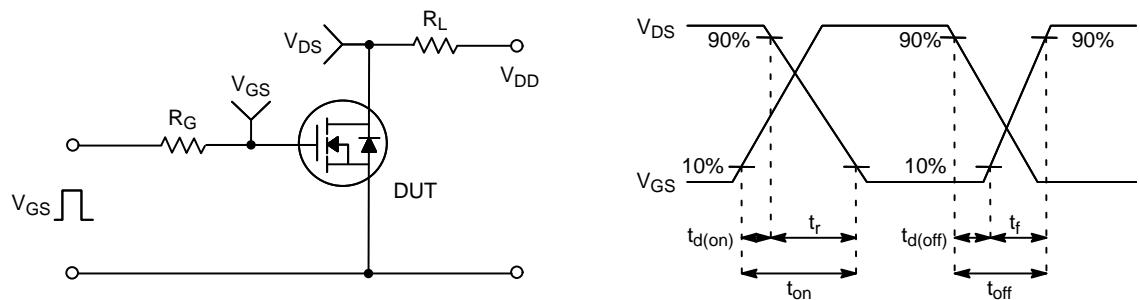


Figure 14. Resistive Switching Test Circuit & Waveforms

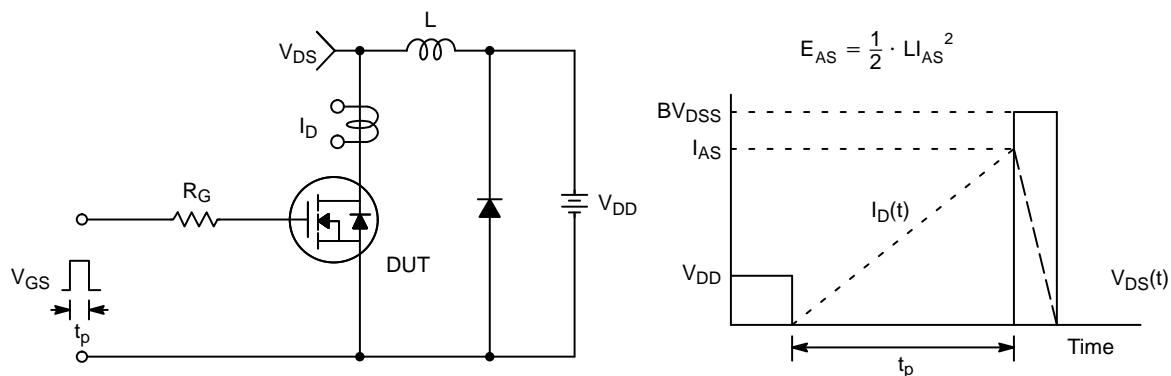


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

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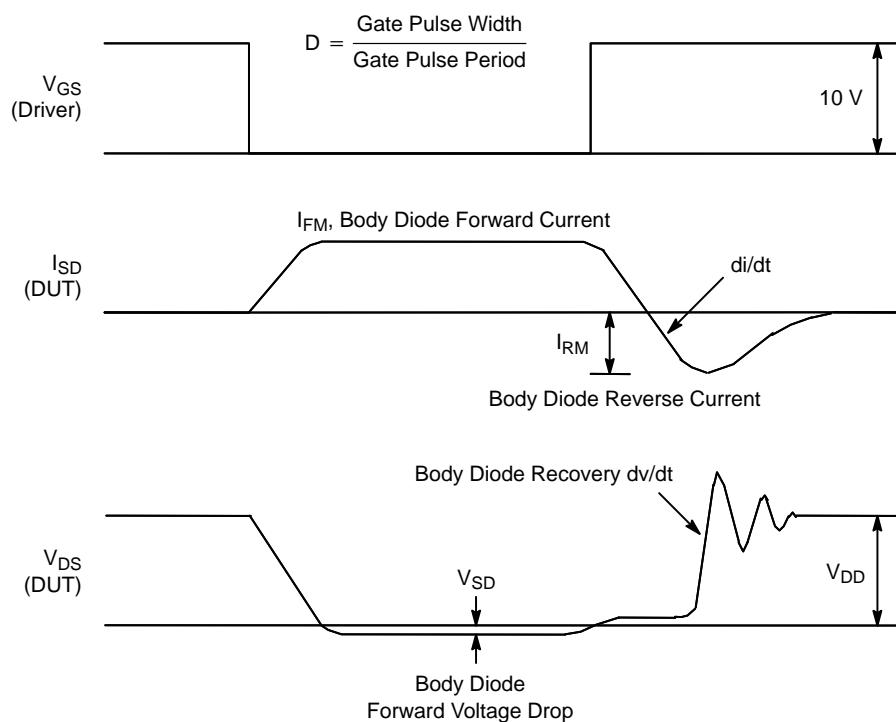
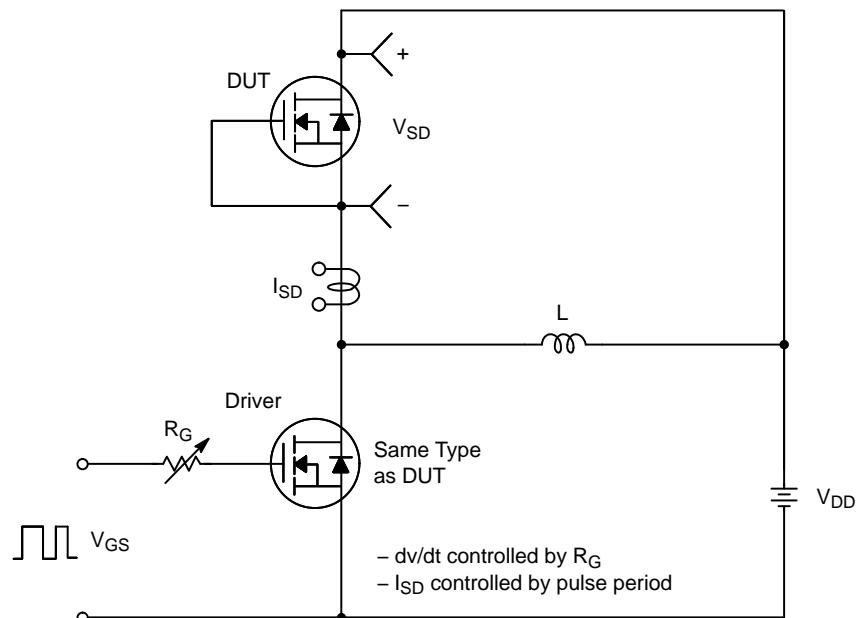


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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MECHANICAL CASE OUTLINE

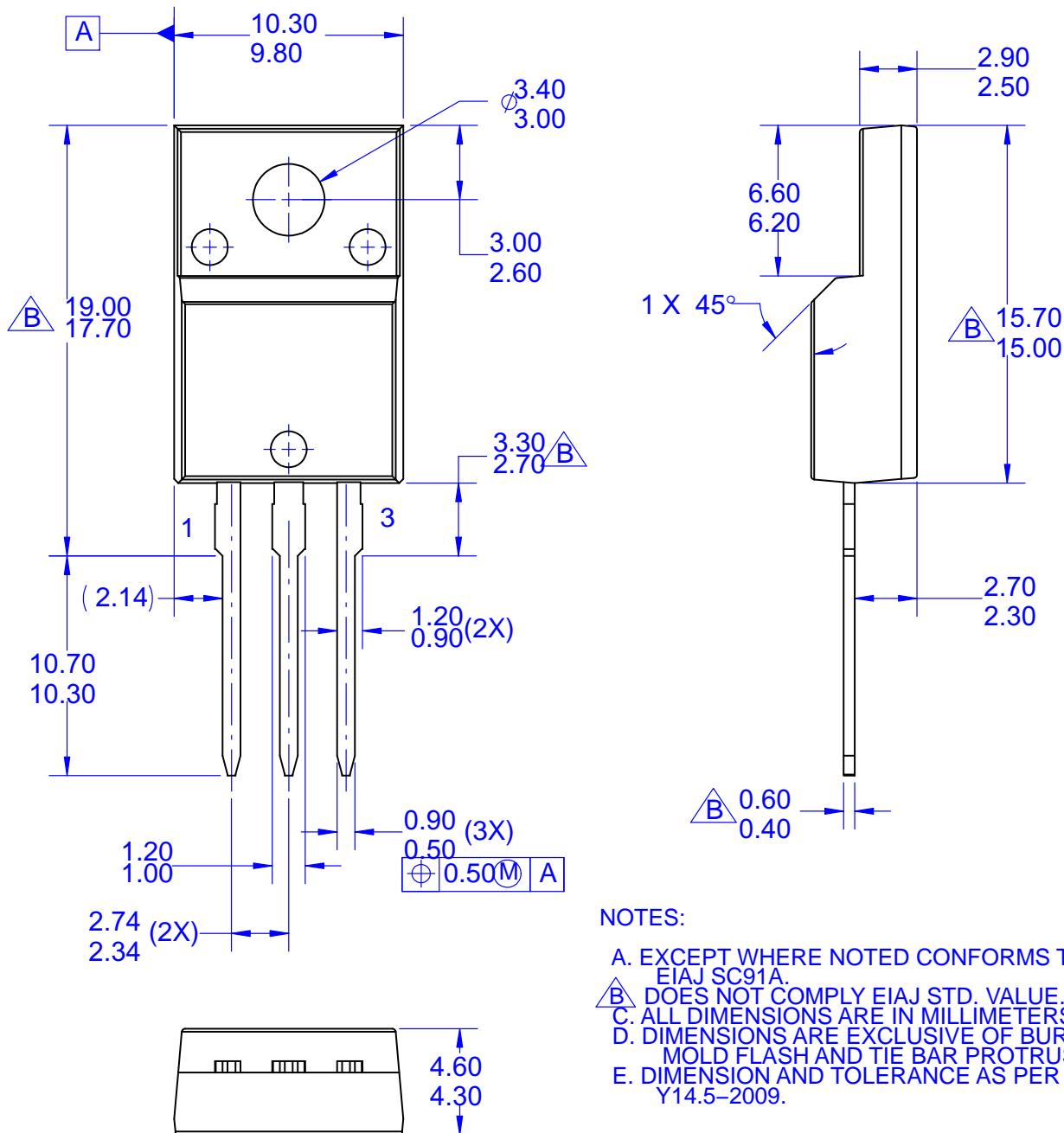
PACKAGE DIMENSIONS

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ON

**TO-220 FULLPAK 3LD
CASE 340BF
ISSUE O**

DATE 31 AUG 2016



NOTES:

A. EXCEPT WHERE NOTED CONFORMS TO
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△ B. DOES NOT COMPLY EIAJ STD. VALUE.

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D. DIMENSIONS ARE EXCLUSIVE OF BURRS,
MOLD FLASH AND TIE BAR PROTRUSIONS.

E. DIMENSION AND TOLERANCE AS PER ASME
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